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Amendments to the Claims

1. (*Currently Amended*) A method of manufacturing a semiconductor device with a semiconductor body and a substrate and comprising,
_____ at least one semiconductor element, ~~which the~~ semiconductor device is equipped with at least one connection region and
_____ a superjacent strip-shaped connection conductor ~~which is~~ connected to the connection region,
_____ ~~which the~~ connection region and the superjacent strip-shaped connection conductor are both recessed in a dielectric, and
_____ a dielectric region of a first material is provided on the semiconductor body at the location of the connection region to be formed, ~~after which~~
_____ the dielectric region is coated with a dielectric layer of a second material that differs from the first material,
_____ ~~which said~~ dielectric layer is provided, at the location of the strip-shaped connection conductor to be formed, with a strip-shaped recess ~~which,~~ viewed in projection, overlaps the dielectric region and extends up to said dielectric region,
_____ and after the formation of the strip-shaped recess and the removal of the dielectric region,
_____ the connection region is formed by depositing an electroconductive material in ~~the space~~ a space obtained by the removal of the dielectric region, and
_____ the strip-shaped connection conductor is formed by depositing an electroconductive material in the strip-shaped recess, characterized in that
_____ for the first material use is made of an organic material, and
_____ for the second material use is made of a material having a higher decomposition temperature than the organic material, and
_____ the dielectric region is removed by heating ~~it at a temperature~~ at a temperature above the decomposition temperature of the organic material yet below the decomposition temperature of the second material.

2. (*Currently Amended*) A method as claimed in claim 1, characterized in that

_____ a photoresist is used as the first material, and
_____ a dielectric resin having a higher decomposition temperature than the photoresist
is used as the second material.

3. (*Currently Amended*) A method as claimed in claim 1, characterized in that
_____ a photoresist is used as the first material, and a liquid glass is used as the second
material, ~~which said~~ liquid glass is converted to solid glass by heating.

4. (*Currently Amended*) A method as claimed in claim 2, characterized in that
_____ the dielectric region is removed during a thermal treatment of the semiconductor
body wherein the liquid glass is converted to solid glass.

5. (*Currently Amended*) A method ~~as claimed in any one of the preceding claims~~, as
claimed in claim 1, characterized in that
the first material as well as the second material are applied in liquid state to the
semiconductor body ~~by means of~~ with a centrifuging process.

6. (*Currently Amended*) A method ~~as claimed in any one of the preceding claims~~, as
claimed in claim 1, characterized in that
_____ the dielectric region is formed by applying a further dielectric layer above which a
mask is provided outside which the further dielectric layer is removed by means of
etching, and the dielectric layer, after deposition, is covered with a mask which is
provided with an aperture at the location of the recess to be formed, after which the
recess is formed by means of etching.

7. (*Currently Amended*) A method ~~as claimed in any one of the preceding claims~~, as
claimed in claim 1, characterized in that
_____ after removal of the dielectric region and after formation of the recess, yet before
deposition of the conductive material, the semiconductor body is cleaned.

8. (*Currently Amended*) A method ~~as claimed in any one of the preceding claims~~, as claimed in claim 1, characterized in that
_____ copper is used as the electroconductive material, and
_____ prior to the deposition of the copper, an electroconductive layer is deposited at the location of the connection region to be formed, ~~which~~ said electroconductive layer forms a barrier for copper.

9. (*Currently Amended*) A method as claimed in claim 8, characterized in that
_____ the electroconductive layer is applied by means of a physical vapor deposition process, and
_____ the copper is provided by means of an electroplating process.

10. (*Currently Amended*) A semiconductor device obtained ~~by means of a method as claimed in any one of the preceding claims~~. by the method of claim 1.